





DUAL 40V PNP SURFACE MOUNT TRANSISTOR

Features

- V_{CEO} = -40V
- I_C = -200mA
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Ultra Small Package

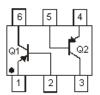
Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)

SOT-963



Top View



Device Schematic

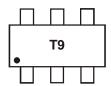
Ordering Information

Device	Packaging	Shipping
DST3906DJ-7	SOT-963	10,000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



T9 = Product Type Marking Code



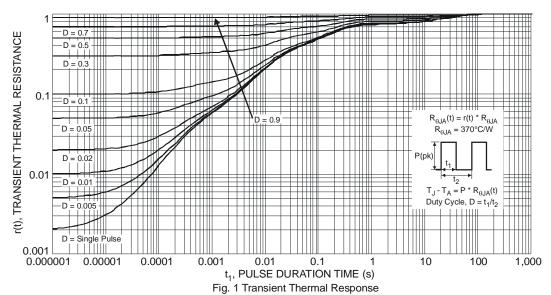
Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 3)	Ic	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB with minimum recommended pad layout.



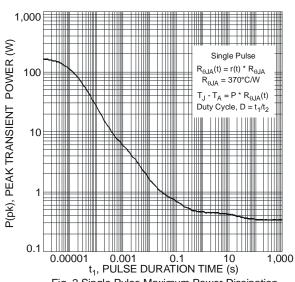


Fig. 2 Single Pulse Maximum Power Dissipation

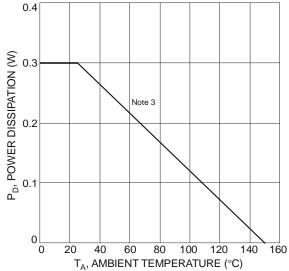


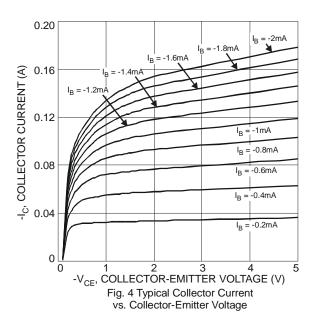
Fig. 3 Power Dissipation vs. Ambient Temperature

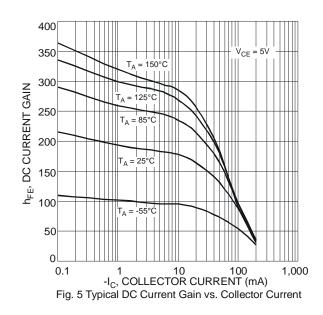


Electrical Characteristics @T_A = 25°C unless otherwise specified

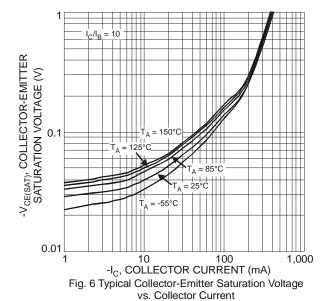
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 4)	V _{(BR)CEO}	-40		V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current			-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Collector Cuton Current	I _{CBO}	_	-50	nA	$V_{CB} = -30V, I_{E} = 0$
Base Cutoff Current	I_{BL}	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 4)					
		60	_		$I_C = -100\mu A, V_{CE} = -1.0V$
		80	_		$I_C = -1.0 \text{mA}, V_{CE} = -1.0 \text{V}$
DC Current Gain	h _{FE}	100	300	_	$I_C = -10 \text{mA}, V_{CE} = -1.0 \text{V}$
		60	_		$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$
		30	_		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	VOE(OAT)		-0.25	V	$I_C = -10mA$, $I_B = -1.0mA$
Collector-Emitter Saturation Voltage	V _{CE} (SAT)	_	-0.40	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65	-0.85		$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$
, and the second		_	-0.95		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	_	4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_{ibo}	_	10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{ie}	2.0	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f _T	300		MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t _r	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t _f		75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

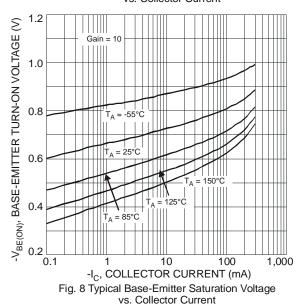
Notes: 4. Short duration pulse test used to minimize self-heating effect.

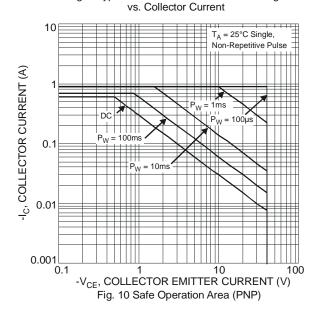


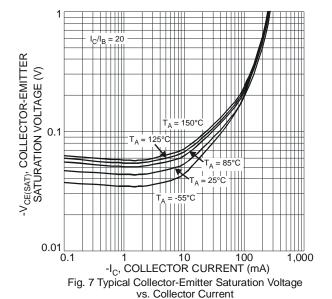








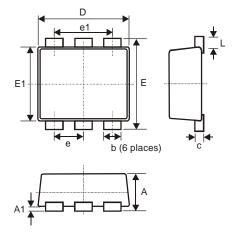




vs. Collector Current

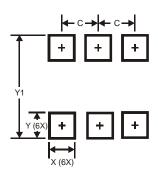


Package Outline Dimensions



SOT-963						
Dim	Min	Max	Тур			
Α	0.40	0.50	0.45			
A1	0	0.05	-			
С	0.120	0.180	0.150			
D	0.95	1.05	1.00			
Е	0.95	1.05	1.00			
E1	0.75	0.85	0.80			
L	0.05	0.15	0.10			
b	0.10	0.20	0.15			
е	0.35 Typ					
e1	0.70 Typ					
All Dimensions in mm						

Suggest Pad Layout



Dimensions	Value (in mm)
С	0.350
Х	0.200
Y	0.200
Y1	1 100



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